A Facile control of major carriers on atomic layer deposited SnO_x thin film by using various oxygen reactants

Figure 1. (a), (b) show saturation growth behavior which mean surface limit reaction mechanism of atomic layer deposition, Growth rate depend on deposition temperature, respectively

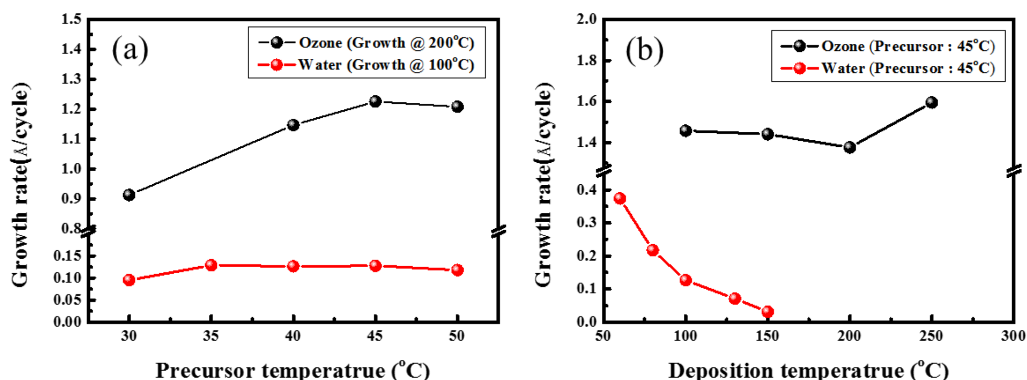

Figure 1. Growth rate of SnOx using Ozone and water depend on (a) precursor and (b) deposition temperature

Figure 2. (a), (b) shows Optical band gap and Refractive index of SnO, SnO_2, respectively

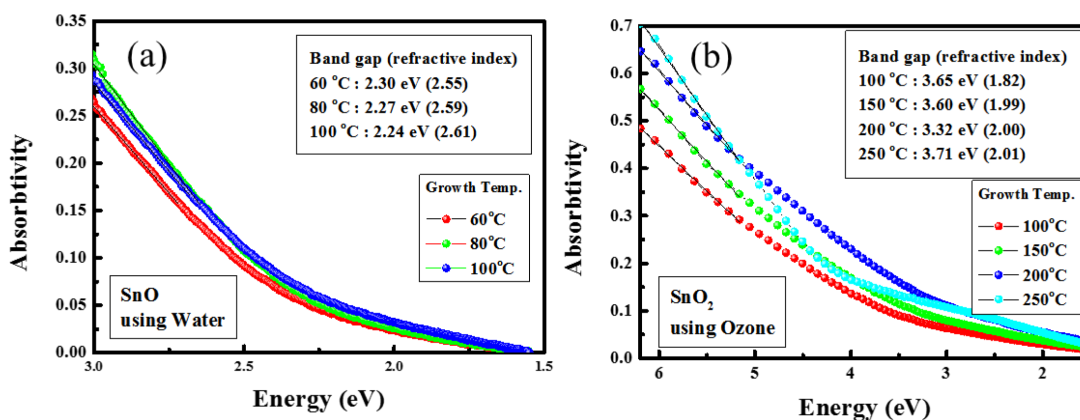

Figure 2. Absorbance and Refractive index of (a) SnO, (b) SnO_2